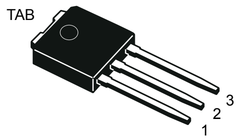
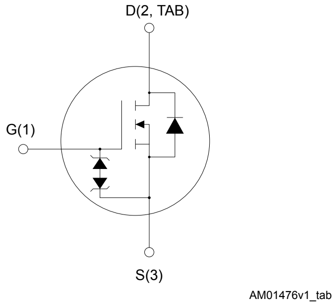
STU6N95K5

Datasheet

N-channel 950 V, 1 Ω typ., 9 A MDmesh K5 Power MOSFET in an IPAK package



IPAK



Features

Order code	V_{DS}	$R_{DS(on)}$ max.	I_D
STU6N95K5	950 V	1.25 Ω	9 A

- Industry's lowest $R_{DS(on)}$ x area
- Industry's best FoM (figure of merit)
- Ultra-low gate charge
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications

Description

This very high voltage N-channel Power MOSFET is designed using MDmesh K5 technology based on an innovative proprietary vertical structure. The result is a dramatic reduction in on-resistance and ultra-low gate charge for applications requiring superior power density and high efficiency.

Product status link
STU6N95K5

Product summary	
Order code	STU6N95K5
Marking	6N95K5
Package	IPAK
Packing	Tube

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	±30	V
I_D	Drain current (continuous) at T_C = 25 °C	9	A
	Drain current (continuous) at T_C = 100 °C	6	
I_{DM}(1)	Drain current (pulsed)	24	A
P_{TOT}	Total power dissipation at T_C = 25 °C	90	W
dv/dt(2)	Peak diode recovery voltage slope	4.5	V/ns
dv/dt(3)	MOSFET dv/dt ruggedness	50	V/ns
T_{stg}	Storage temperature range	-55 to 150	°C
T_J	Operating junction temperature range		°C

1. *Pulse width is limited by safe operating area.*
2. *$I_{SD} \leq 9$ A, di/dt ≤ 100 A/μs, V_{DS} (peak) < $V_{(BR)DSS}$.*
3. *$V_{DS} \leq 760$ V.*

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance, junction-to-case	1.39	°C/W
R_{thJA}	Thermal resistance, junction-to-ambient	100	°C/W

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or non-repetitive (pulse width limited by T_J max.)	3	A
E_{AS}	Single pulse avalanche energy (starting T_J = 25 °C, I_D = I_{AR}, V_{DD} = 50 V)	90	mJ

2 Electrical characteristics

T_C = 25 °C unless otherwise specified.

Table 4. **On/off-state**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS} = 0 V, I_D = 1 mA	950			V
I_{DSS}	Zero gate voltage drain current	V_{DS} = 950 V, V_{GS} = 0 V			1	µA
		V_{DS} = 950 V, V_{GS} = 0 V, T_C = 125 °C(1)			50	
I_{GSS}	Gate body leakage current	V_{GS} = ±20 V, V_{DS} = 0 V			±10	µA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 100 µA	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D = 3 A		1	1.25	Ω

1. *Specified by design, not tested in production.*

Table 5. **Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS} = 100 V, f = 1 MHz, V_{GS} = 0 V	-	430	-	pF
C_{oss}	Output capacitance		-	36	-	pF
C_{rss}	Reverse transfer capacitance		-	1	-	pF
$C_{o(tr)}$(1)	Equivalent capacitance time related	V_{GS} = 0 V, V_{DS} = 0 to 760 V	-	52	-	pF
$C_{o(er)}$(2)	Equivalent capacitance energy related		-	19	-	pF
R_g	Intrinsic gate resistance	f = 1 MHz, I_D = 0 A	-	7	-	Ω
Q_g	Total gate charge	V_{DD} = 760 V, I_D = 6 A, V_{GS} = 0 to 10 V (see Figure 15. Test circuit for gate charge behavior)	-	9.6	-	nC
Q_{gs}	Gate-source charge		-	3.2	-	nC
Q_{gd}	Gate-drain charge		-	4.4	-	nC

1. *$C_{o(tr)}$ is a constant capacitance value that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.*
2. *$C_{o(er)}$ is a constant capacitance value that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.*

Table 6. **Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD}= 475 V, I_D = 3 A, R_G = 4.7 Ω, V_{GS} = 10 V (see Figure 14. Test circuit for resistive load switching times and Figure 19. Switching time waveform)	-	12	-	ns
t_r	Rise time		-	12	-	ns
$t_{d(off)}$	Turn-off delay time		-	33	-	ns
t_f	Fall time		-	21	-	ns

Table 7. **Source-drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		9	A
I_{SDM} (1)	Source-drain current (pulsed)		-		24	A
V_{SD}(2)	Forward on voltage	I_{SD} = 6 A, V_{GS} = 0 V	-		1.6	V
t_{rr}	Reverse recovery time	I_{SD} = 6 A, di/dt = 100 A/μs, V_{DD} = 60 V (see Figure 16. Test circuit for inductive load switching and diode recovery times)	-	372		ns
Q_{rr}	Reverse recovery charge		-	4		μC
I_{RRM}	Reverse recovery current		-	22		A
t_{rr}	Reverse recovery time	I_{SD} = 6 A, di/dt = 100 A/μs, V_{DD} = 60 V, T_J= 150 °C (see Figure 16. Test circuit for inductive load switching and diode recovery times)	-	522		ns
Q_{rr}	Reverse recovery charge		-	5		μC
I_{RRM}	Reverse recovery current		-	20		A

1. *Pulse width is limited by safe operating area.*
2. *Pulsed: pulse duration = 300 μs, duty cycle 1.5%.*

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

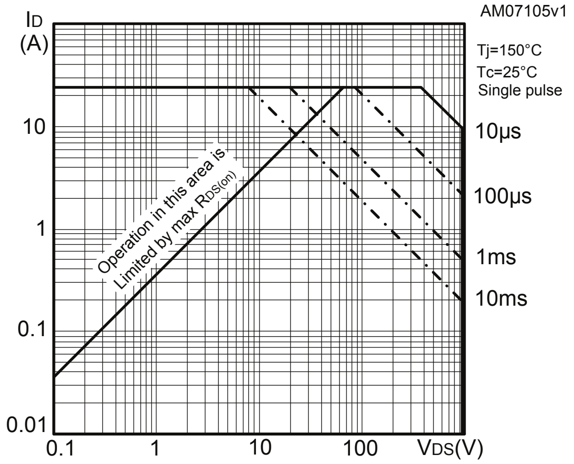


Figure 2. Normalized transient thermal impedance

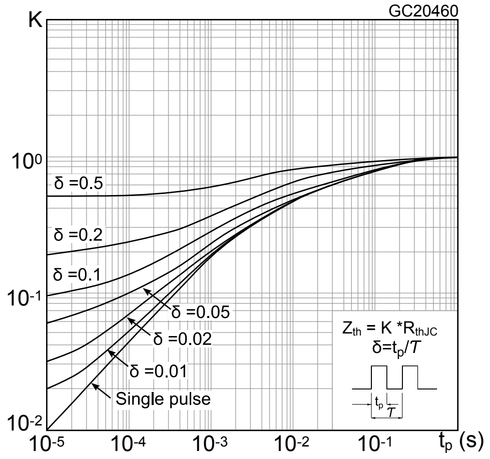


Figure 3. Typical output characteristics

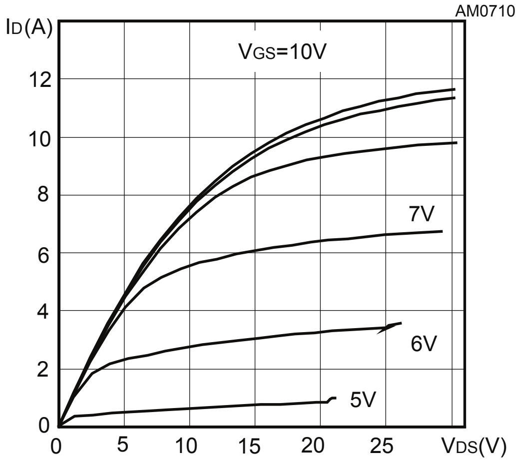


Figure 4. Typical transfer characteristics

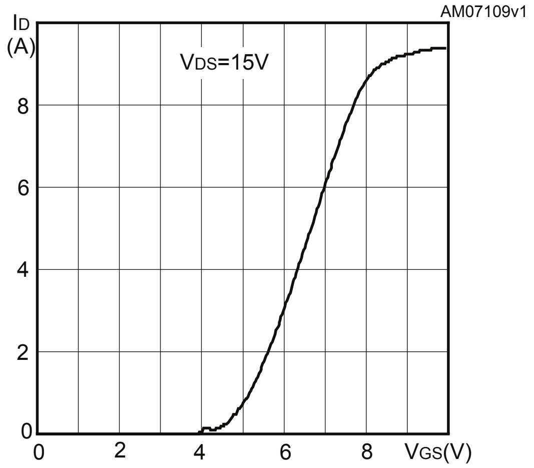


Figure 5. Typical gate charge characteristics

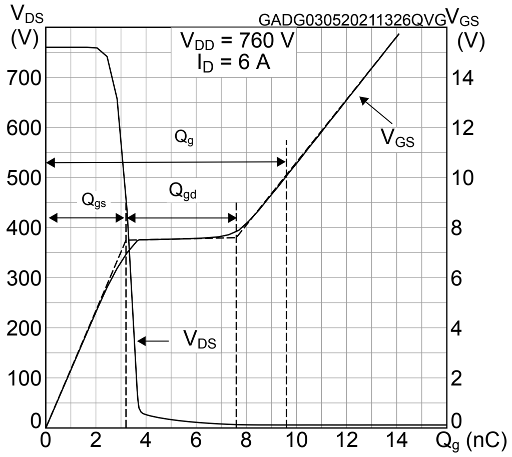


Figure 6. Typical drain-source on-resistance

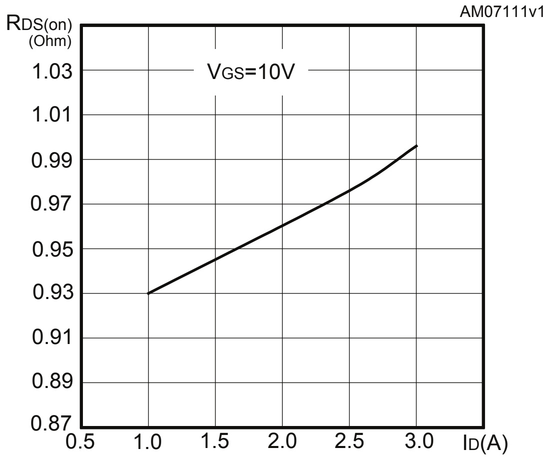


Figure 7. Typical capacitance characteristics

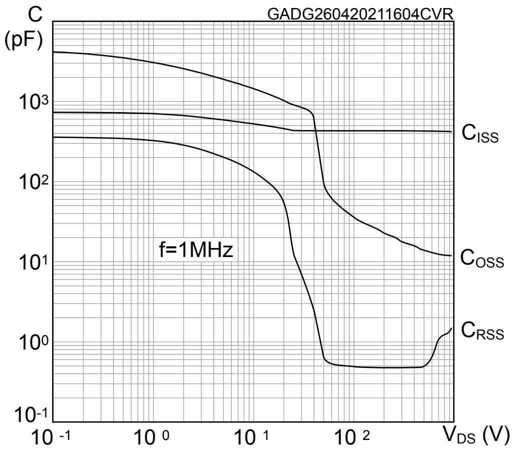


Figure 8. Output capacitance stored energy

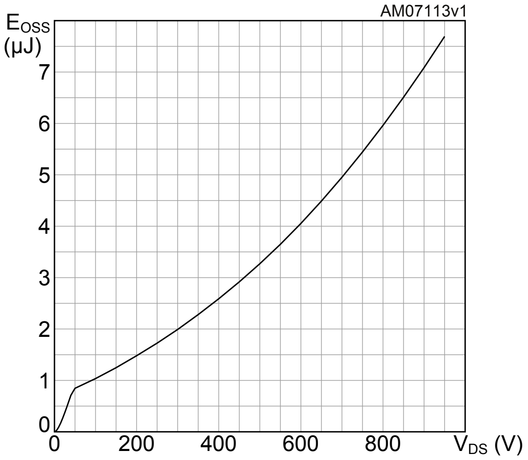


Figure 9. Normalized gate threshold vs temperature

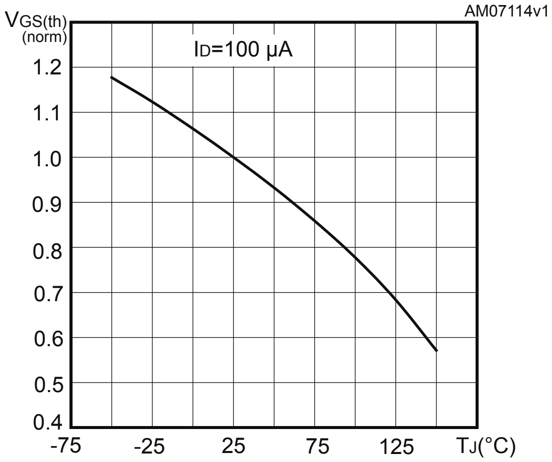


Figure 10. Normalized on-resistance vs temperature

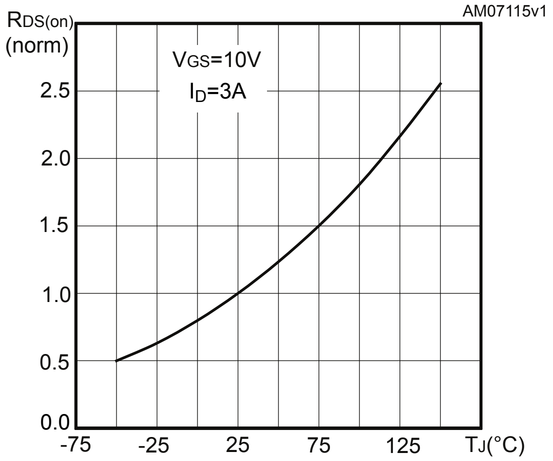


Figure 11. Typical drain-source on-resistance

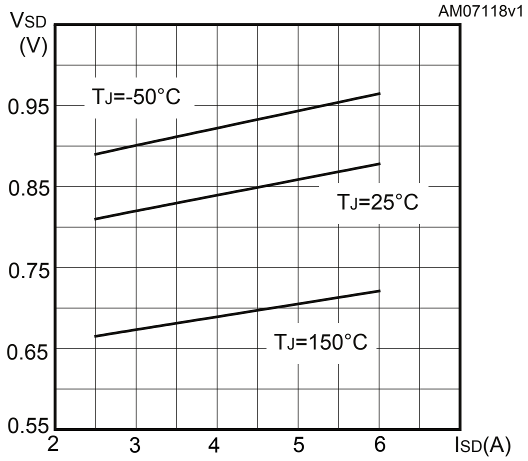


Figure 12. Normalized breakdown voltage vs temperature

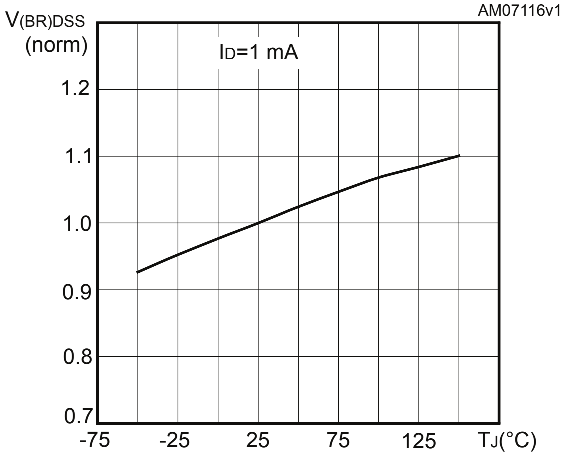
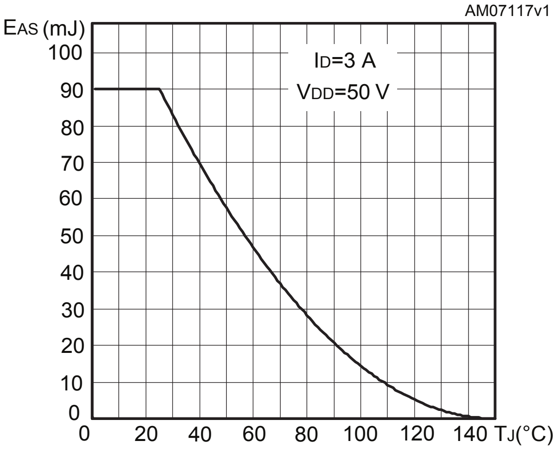


Figure 13. Maximum avalanche energy vs temperature



3 Test circuits

Figure 14. Test circuit for resistive load switching times

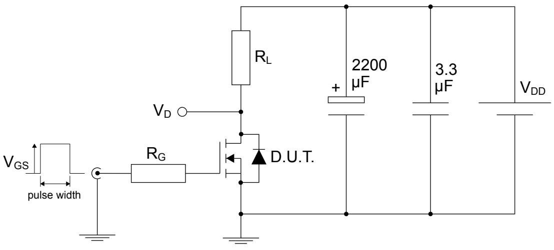


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Figure 15. Test circuit for gate charge behavior

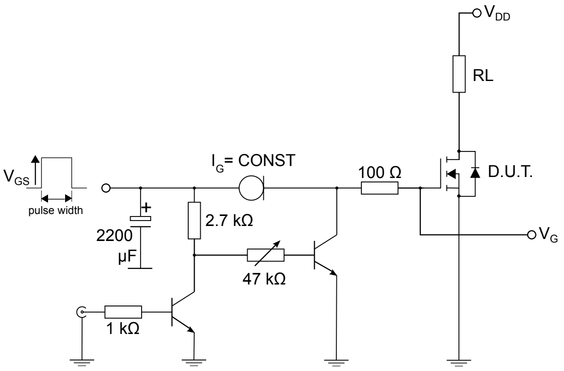

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Figure 16. Test circuit for inductive load switching and diode recovery times

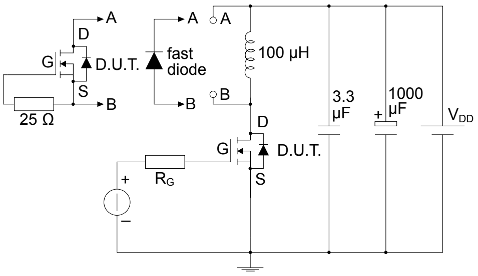

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Figure 17. Unclamped inductive load test circuit

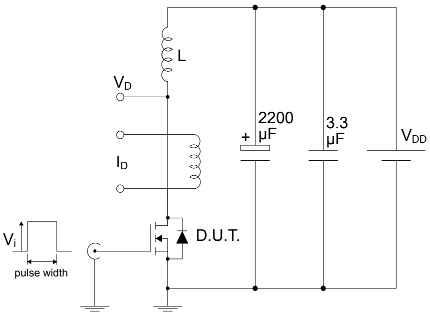

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Figure 18. Unclamped inductive waveform

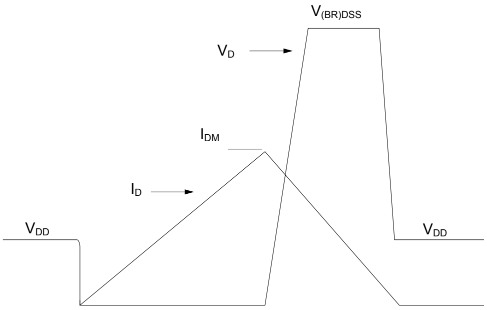

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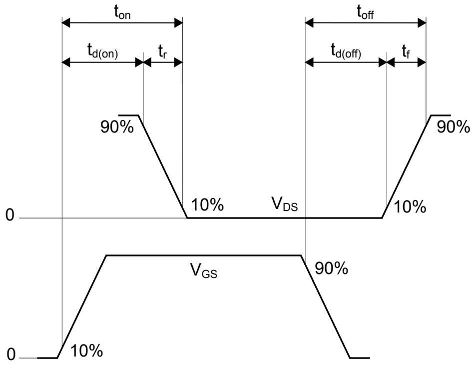
Figure 19. Switching time waveform



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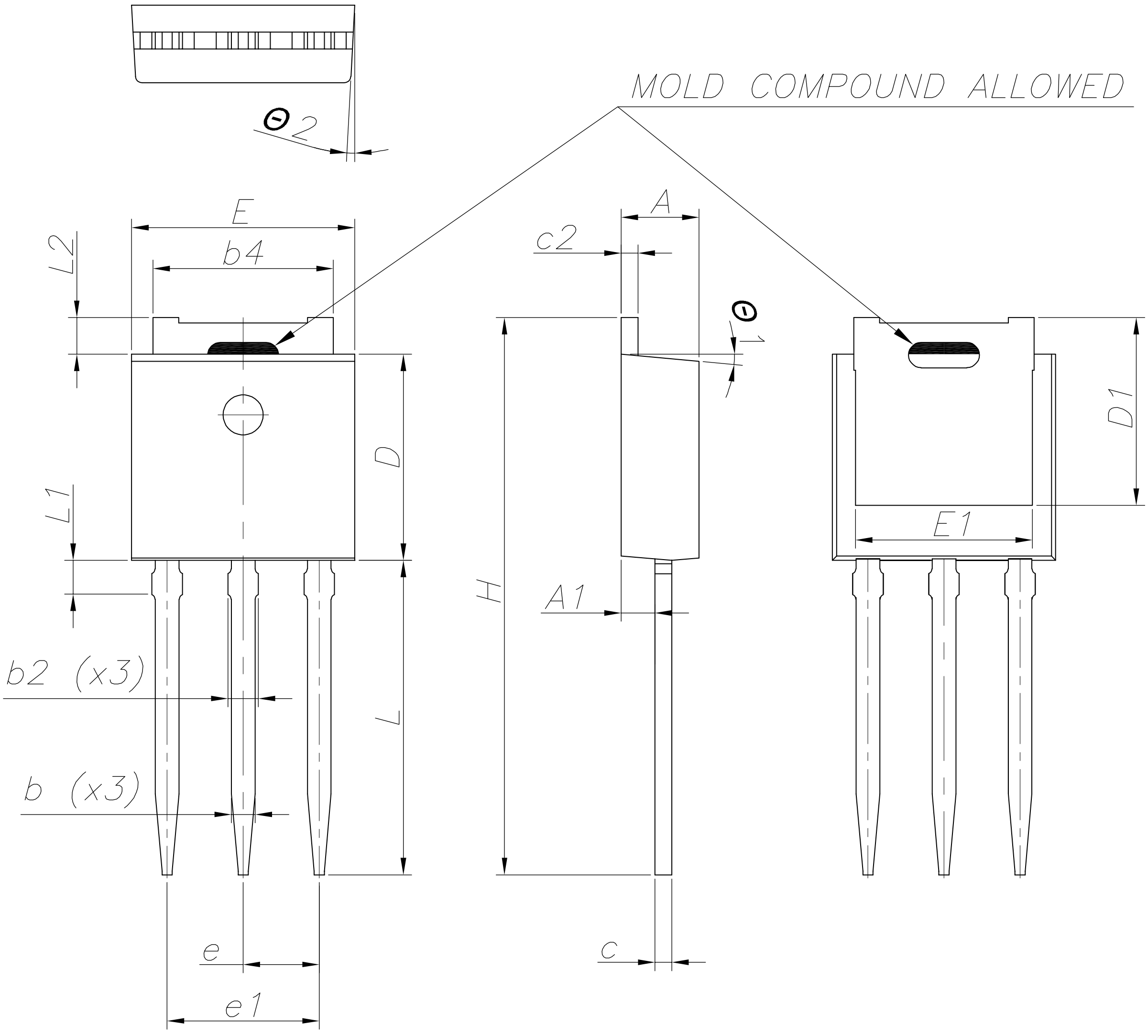
4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 IPAK (TO-251) type E package information

Figure 20. IPAK (TO-251) type E package outline



0068771_E_rev.16

Table 8. **IPAK (TO-251) type E package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	2.20	2.30	2.35
A1	0.90	1.00	1.10
b	0.66		0.79
b2			0.90
b4	5.23	5.33	5.43
c	0.46		0.59
c2	0.46		0.59
D	6.00	6.10	6.20
D1	5.30	5.53	5.75
E	6.50	6.60	6.70
E1	5.05	5.23	5.40
e	2.20	2.25	2.30
e1	4.40	4.50	4.60
H	16.18	16.48	16.78
L	9.00	9.30	9.60
L1	0.80	1.00	1.20
L2	0.90	1.08	1.25
Θ1	3°	5°	7°
Θ2	1°	3°	5°

Revision history

Table 9. **Document revision history**

Date	Revision	Changes
02-Oct-2023	1	First release. Part number STU6N95K5 previously included in datasheet DS6666.

Contents

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